

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|--|---|---------------------|
| 1 | 403 | (sputtering near2 target) same (niobium Nb Cb columbian) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2002/03/25 15:22 |
| 2 | 75 | (sputtering near2 target) near5 (niobium Nb Cb columbian) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2002/03/25 15:23 |

DOCUMENT-IDENTIFIER: US 5830569 A

TITLE: Magnetic recording medium containing CoPtO-based alloy magnetic film

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DEPR:

In addition, an Nb film having a thickness of 21 nm was formed on a glass substrate by sputtering. In sputtering, an Nb target having an outer diameter of 5 inches was used. The target-to-substrate distance was 150 mm, the sputtering pressure was 0.6 Pa, and the applied power was 2 kW. Subsequently, a carbon film having a thickness of 9 nm was formed on the Nb film by sputtering. In sputtering, a carbon target having an outer diameter of 5 inches was used. The target-to-substrate distance was 150 mm, the sputtering pressure was 2 Pa, and the applied power was 1 kW. A CoPtCrO film having a thickness of 5 nm-20 nm and containing 25 atomic % of oxygen was formed on the Nb film by the same method as described above. In this manner, various magnetic recording media with magnetic films having different thicknesses were prepared by forming CoPtCrO films on glass substrates through carbon films and Nb films.

DEPR:

A V-Nb film having a thickness of 50 nm was formed on a glass substrate by sputtering. In sputtering, a V target and an Nb target, both of which had an outer diameter of 5 inches, were used. The target-to-substrate distance was 120 mm, the sputtering pressure was 0.3 Pa. For the V-Nb film, the applied power in sputtering was controlled to form films having various compositions.

DEPR:

An Nb film having a thickness of 21 nm was formed as a first underlayer on a glass substrate by sputtering. In sputtering, an Nb target having an outer diameter of 5 inches was used. The target-to-substrate distance was 170 mm, the sputtering pressure was 2 Pa, and the applied power was 2.5 kW. The 21-nm thickness of the Nb film is a value for obtaining a sufficient crystal orientation.

DEPR:

An Nb film having a thickness of 21 nm was formed as a first underlayer on a glass substrate by sputtering. In sputtering, an Nb target having an outer diameter of 5 inches was used. The target-to-substrate distance was 170 mm, the sputtering pressure was 0.6 Pa, and the applied power was 2.5 kW. The 21-nm thickness of the Nb film is a value for obtaining a sufficient crystal orientation.

DOCUMENT-IDENTIFIER: US 5661345 A
TITLE: Semiconductor device having a single-crystal metal wiring

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DEPR:

Next, with reference to FIG. 11B, an Nb (niobium) thin film 22 was formed on the BPSG film 12 by a d.c. magnetron sputtering method without annealing thereon. Then, Nb with purity 99.9999% was used for a sputtering target, and Nb was formed at thickness of 50 nm. Ar was a gas that was utilized in the sputtering, a background pressure was less than 10^{-8} Torr, a pressure under sputtering was 3×10^{-3} Torr, and an applied power was 1 KW. Thereafter, with reference to FIG. 11C, Nb film located at other than the groove was removed.

DOCUMENT-IDENTIFIER: US 5409862 A

TITLE: Method for making aluminum single crystal interconnections on insulators

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DEPR:

Next, with reference to FIG. 11B, an Nb (niobium) thin film 22 was formed on the BPSG film 12 by a d.c. magnetron sputtering method without annealing thereon. Then, Nb with purity 99.9999% was used for a sputtering target, and Nb was formed at thickness of 50 nm. Ar was a gas that was utilized in the sputtering, a background pressure was less than 10^{-8} Torr, a pressure under sputtering was 3×10^{-3} Torr, and an applied power was 1 KW. Thereafter, with reference to FIG. 11C, Nb film located at other than the groove was removed.